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### 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- Average forward current:  $I_{F(AV)} \le 10 \text{ A}$
- Reverse voltage: V<sub>R</sub> ≤ 45 V
- Low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

### 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 130 °C; square wave	-	-	10	A
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C	-	-	45	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C; pulsed	-	473	540	mV
I <sub>R</sub>	reverse current	$V_R$ = 10 V; $t_p \le 3$ ms; $\delta$ = 0.3; $T_j$ = 25 °C; pulsed	-	13	30	μA
		$\label{eq:VR} \begin{array}{l} V_R = 45 \; V; \; t_p \leq 3 \; ms; \; \delta = 0.3; \\ T_j = 25 \; ^\circC; \; pulsed \end{array}$	-	150	500	μA





45 V, 10 A low VF MEGA Schottky barrier rectifier

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		
2	А	anode		
3	к	cathode	(2) CFP15 (SOT1289)	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PMEG45A10EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: $5.8 \times 4.3 \times 0.78 \text{ mm}$	SOT1289

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG45A10EPD	4510 AAAA

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	45	V
l <sub>F</sub>	forward current	T <sub>sp</sub> = 125 °C; δ = 1		-	14	А
I <sub>F(AV)</sub>	average forward current	δ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 130 °C; square wave		-	10	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	170	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.9	W
			[2]	-	1.2	W
			[3]	-	3	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C

#### 45 V, 10 A low VF MEGA Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

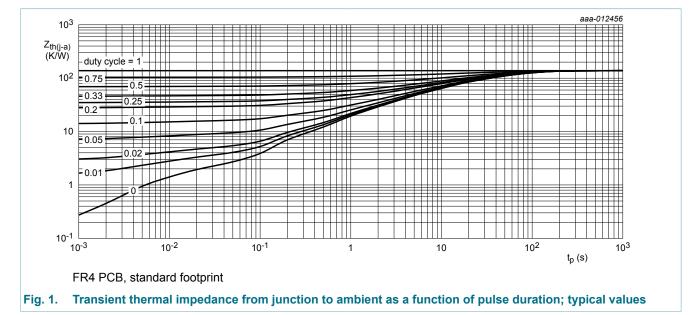
[3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

### 9. Thermal characteristics

Table 6. The	Fable 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	165	K/W
from junction to ambient			[1][3]	-	-	120	K/W
	ampient		[1][4]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	4	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses.

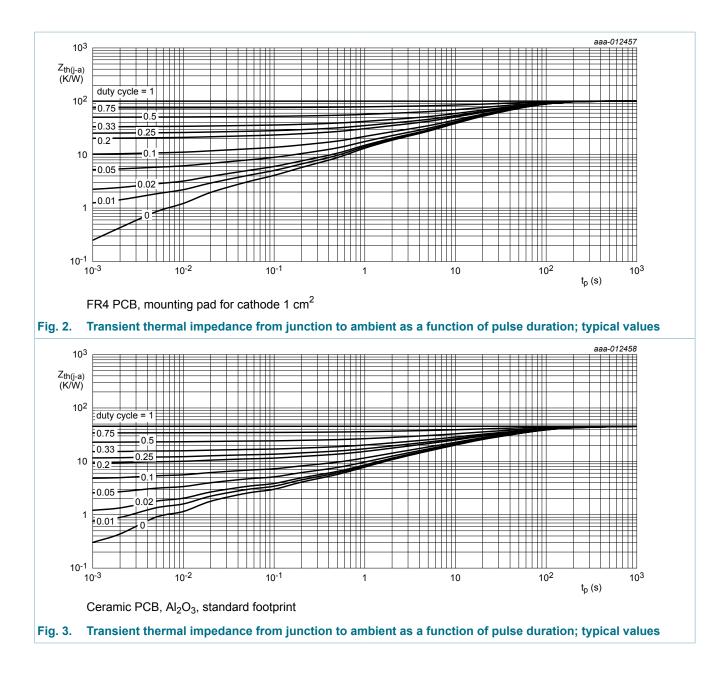
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.



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## PMEG45A10EPD

#### 45 V, 10 A low VF MEGA Schottky barrier rectifier



PMEG45A10EPD

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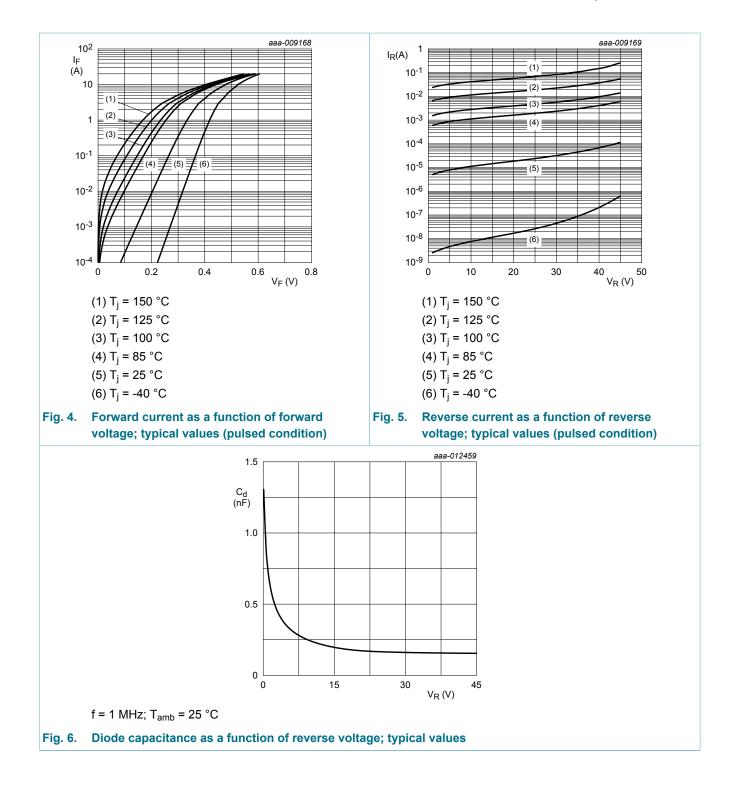
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 1 A; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02; T <sub>j</sub> = 25 °C; pulsed	-	330	380	mV
		$I_F$ = 2 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	357	-	mV
		$I_F$ = 3 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	377	-	mV
		$I_F$ = 5 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	409	470	mV
		$I_{F} = 10 \text{ A}; t_{p} \le 300  \mu\text{s}; \delta \le 0.02;$ $T_{j} = 25 \text{ °C}; \text{ pulsed}$	-	473	540	mV
I <sub>R</sub> reve	reverse current	$V_{R}$ = 5 V; $t_{p}$ ≤ 3 ms; $\delta$ = 0.3; $T_{j}$ = 25 °C; pulsed	-	10	-	μA
		$V_R$ = 10 V; $t_p \le 3$ ms; $\delta$ = 0.3; $T_j$ = 25 °C; pulsed	-	13	30	μA
		$V_R$ = 30 V; $t_p \le$ 3 ms; $\delta$ = 0.3; $T_j$ = 25 °C; pulsed	-	36	-	μA
		$V_R$ = 45 V; $t_p \le 3$ ms; $\delta$ = 0.3; $T_j$ = 25 °C; pulsed	-	150	500	μA
		$V_R$ = 10 V; $t_p \le 3$ ms; $\delta$ = 0.3; $T_j$ = 125 °C; pulsed	-	11	-	mA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	715	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	240	-	pF
t <sub>rr</sub>	reverse recovery time ; step recovery	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	21	-	ns
trr	reverse recovery time ; ramp recovery	dI <sub>F</sub> /dt = 200 A/µs; T <sub>j</sub> = 25 °C; I <sub>F</sub> = 6 A; V <sub>R</sub> = 26 V	-	13	-	ns
V <sub>(BR)R</sub>	reverse breakdown voltage	$I_R$ = 5 mA; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 1.2 ms; δ = 0.12; pulsed	45	-	-	V
V <sub>FRM</sub>	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; \text{ T}_j = 25 ^\circ\text{C}$	-	317	-	mV

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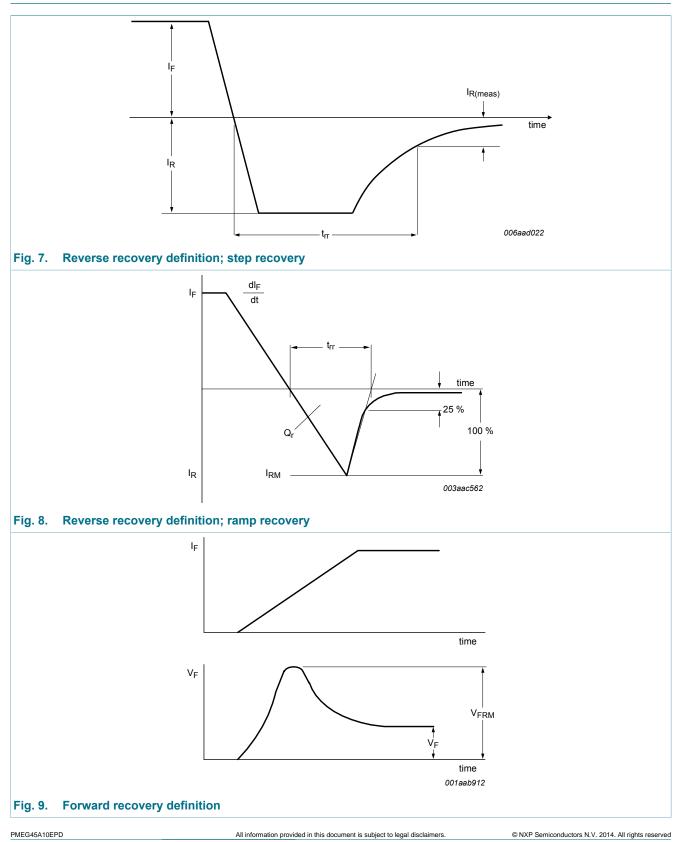
# PMEG45A10EPD

#### 45 V, 10 A low VF MEGA Schottky barrier rectifier

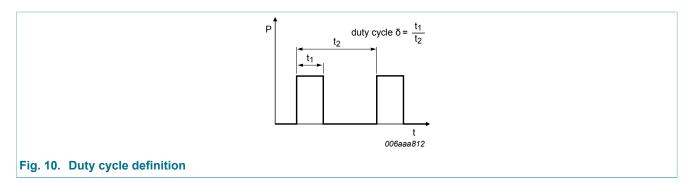


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### **11. Test information**

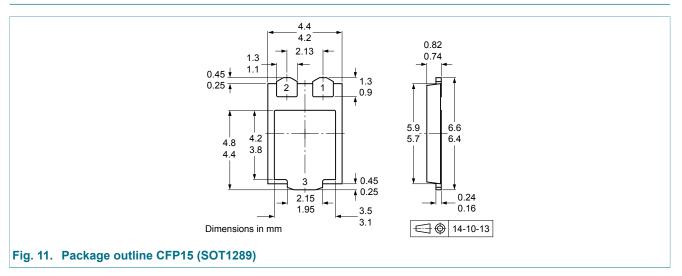


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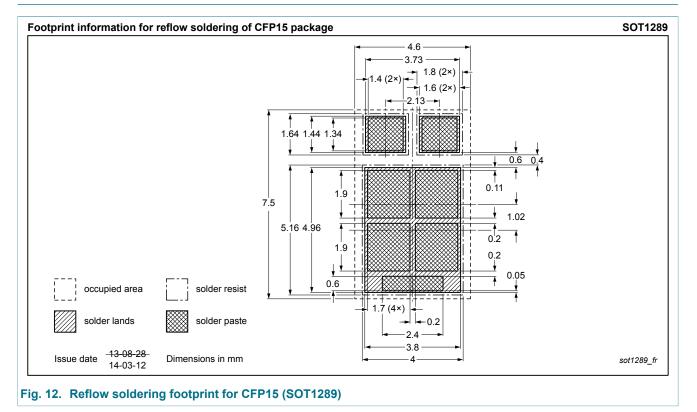
The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 12. Package outline



#### 45 V, 10 A low VF MEGA Schottky barrier rectifier

### **13. Soldering**



45 V, 10 A low VF MEGA Schottky barrier rectifier

## 14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG45A10EPD v.3	20141216	Product data sheet	-	PMEG45A10EPD v.2
Modifications:	Package outline dra	awing updated		
PMEG45A10EPD v.2	20140416	Product data sheet	-	PMEG45A10EPD v.1
PMEG45A10EPD v.1	20140217	Objective data sheet	-	-

#### 45 V, 10 A low VF MEGA Schottky barrier rectifier

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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